

10A Avg.

35 Volts

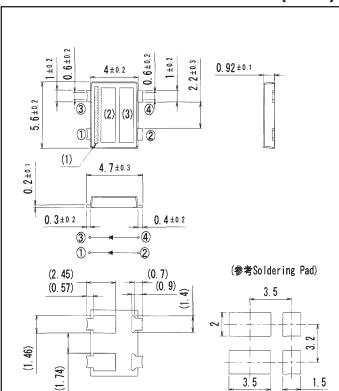
SBD

NB10QSA035

■最大定格 Maximum Ratings

Item	Symbol	Conditions		Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V _{RRM}	35		V
平均整流電流 Average Rectified Forward Current	I _O	50Hz、正弦半波通電抵抗負荷 50Hz Half Sine Wave Resistive Load *1	T _a =26°C ^{*2} V _{RM} =15V	3.7 A
			T _l =105°C T _{lead} Temperature V _{RM} =15V	10 A
実効順電流 R.M.S. Forward Current	I _{F(RMS)}	11.1		A
サージ順電流 Surge Forward Current	I _{FSM}	100 50Hz正弦半波、1サイクル、非くり返し 50Hz Half Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	T _{jw}	−40～+150		°C
保存温度範囲 Storage Temperature Range	T _{stg}	−40～+150		°C

■OUTLINE DRAWING(mm)



■APPROX. NET WEIGHT:0.06 g

■電気的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions		Min.	Typ.	Max.	Unit
ピーケ逆電流 Peak Reverse Current	I _{RM}	T _j =25°C, V _{RM} =35V, *1素子あたり Per Diode		—	—	3	mA
ピーケ順電圧 Peak Forward Voltage	V _{FM}	T _j =25°C, I _{FM} =5A, *1素子あたり Per Diode		—	—	0.57	V
熱抵抗 Thermal Resistance	R _{th(j-a)}	接合部・周囲間 Junction to Ambient	*2 ガラエボ基板実装 Glass-Epoxy Substrate mounted	—	—	60	°C/W
	R _{th(j-l)}	接合部・リード間 Junction to Lead	—	—	—	7	°C/W

*1 カソードコモン動作による/Common Cathode Operation

*2 ガラエボ基板実装/Glass-Epoxy Substrate mounted (Soldering Lands= 2.0 × 1.5 mm, 2.0 × 3.5 mm, Both Sides)

■定格・特性曲線

